

# **BUK9Y15-100E**

### N-channel 100 V, 15 m $\Omega$ logic level MOSFET in LFPAK56 Product data sheet

#### 1. **General description**

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### 2. **Features and benefits**

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V<sub>GS(th)</sub> rating of greater than 0.5 V at 175 °C

## **Applications**

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

#### Quick reference data

Quick reference data Table 1.

| Symbol            | Parameter                        | Conditions  | Min | Тур  | Max | Unit |
|-------------------|----------------------------------|---|-----|------|-----|------|
| V <sub>DS</sub>   | drain-source voltage             | 25 °C ≤ T <sub>j</sub> ≤ 175 °C   | -   | -    | 100 | V    |
| I <sub>D</sub>    | drain current                    | V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig.</u>                               | -   | -    | 69  | Α    |
| P <sub>tot</sub>  | total power dissipation          | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>  | -   | -    | 195 | W    |
| Static charact    | eristics                         |   |     |      |     |      |
| R <sub>DSon</sub> | drain-source on-state resistance | $V_{GS} = 5 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$                  | -   | 12.1 | 15  | mΩ   |
| Dynamic char      | acteristics                      |   |     |      |     |      |
| $Q_{GD}$          | gate-drain charge                | I <sub>D</sub> = 20 A; V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 5 V;<br>Fig. 13; Fig. 14 | -   | 16   | -   | nC   |



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# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline                         | Graphic symbol |
|-----|--------|-----------------------------------|--|----------------|
| 1   | S      | source                            | mb   | D<br>I         |
| 2   | S      | source                            | <u> </u>                                   |                |
| 3   | S      | source                            | q j  | G_U: 4         |
| 4   | G      | gate                              | و و و و                                    | mbb076 S       |
| mb  | D      | mounting base; connected to drain | 1 2 3 4<br>LFPAK56; Power-<br>SO8 (SOT669) |                |

# 6. Ordering information

Table 3. Ordering information

| Type number  | Package               |  |         |  |  |
|--------------|-----------------------|--|---------|--|--|
|              | Name                  | Description  | Version |  |  |
| BUK9Y15-100E | LFPAK56;<br>Power-SO8 | Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads | SOT669  |  |  |

# 7. Marking

Table 4. Marking codes

| Type number  | Marking code |
|--------------|--------------|
| BUK9Y15-100E | 91510E       |

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions   |        | Min | Max | Unit |
|------------------|-------------------------|--|--------|-----|-----|------|
| V <sub>DS</sub>  | drain-source voltage    | 25 °C ≤ T <sub>j</sub> ≤ 175 °C                                |        | -   | 100 | V    |
| $V_{DGR}$        | drain-gate voltage      | $R_{GS}$ = 20 k $\Omega$                                       |        | -   | 100 | V    |
| $V_{GS}$         | gate-source voltage     | DC; T <sub>j</sub> ≤ 175 °C                                    |        | -10 | 10  | V    |
|                  |                         | Pulsed; T <sub>j</sub> ≤ 175 °C                                | [1][2] | -15 | 15  | V    |
| P <sub>tot</sub> | total power dissipation | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>                         |        | -   | 195 | W    |
| I <sub>D</sub>   | drain current           | $V_{GS} = 5 \text{ V}; T_{mb} = 25 ^{\circ}\text{C}; Fig. 2$   |        | -   | 69  | Α    |
|                  |                         | V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u> |        | -   | 49  | Α    |
| I <sub>DM</sub>  | peak drain current      | pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; Fig. 3 |        | -   | 274 | Α    |

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| Symbol               | Parameter                                    | Conditions   |        | Min | Max | Unit |
|----------------------|--|--|--------|-----|-----|------|
| T <sub>stg</sub>     | storage temperature                          |  |        | -55 | 175 | °C   |
| T <sub>j</sub>       | junction temperature                         |  |        | -55 | 175 | °C   |
| Source-drain         | diode  |  |        |     |     |      |
| I <sub>S</sub>       | source current                               | T <sub>mb</sub> = 25 °C  |        | -   | 69  | Α    |
| I <sub>SM</sub>      | peak source current                          | pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$   |        | -   | 274 | Α    |
| Avalanche ruggedness |  |  |        |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | $I_D$ = 69 A; $V_{sup}$ ≤ 100 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4 | [3][4] | -   | 110 | mJ   |

- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering T<sub>i</sub> and or V<sub>GS</sub>
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.

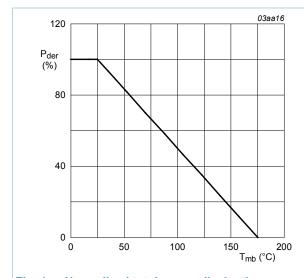


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

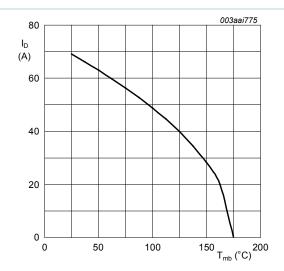


Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$

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#### N-channel 100 V, 15 m $\Omega$ logic level MOSFET in LFPAK56

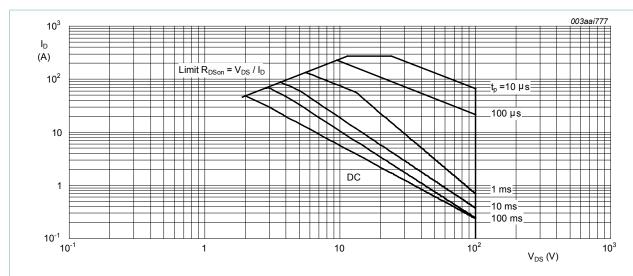
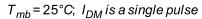


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



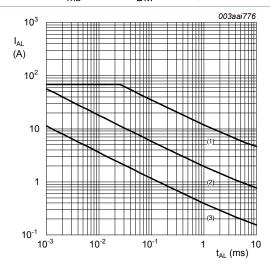


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1) 
$$T_{j(init)} = 25$$
°C; (2)  $T_{j(init)} = 150$ °C; (3) Repetitive Avalanche

#### 9. Thermal characteristics

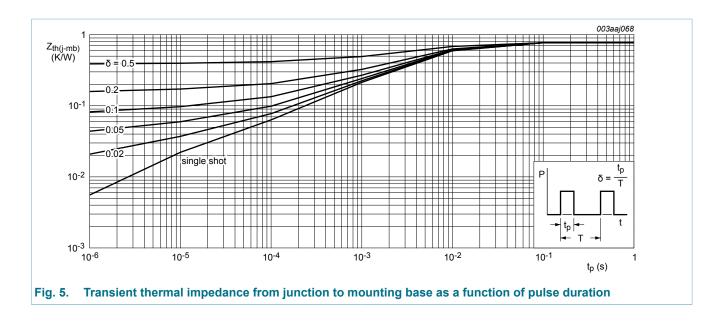
Table 6. Thermal characteristics

| Symbol                | Parameter   | Conditions | Min | Тур | Max  | Unit |
|-----------------------|---|------------|-----|-----|------|------|
| R <sub>th(j-mb)</sub> | thermal resistance<br>from junction to<br>mounting base | Fig. 5     | -   | _   | 0.77 | K/W  |

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## 10. Characteristics

Table 7. Characteristics

| Symbol               | Parameter                     | Conditions  |  | Min | Тур  | Max  | Unit |
|----------------------|-------------------------------|---|--|-----|------|------|------|
| Static char          | acteristics                   |   |  |     |      |      |      |
| V <sub>(BR)DSS</sub> | drain-source                  | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 ^{\circ}C$   |  | 100 | -    | -    | V    |
|                      | breakdown voltage             | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$   |  | 90  | -    | -    | V    |
| $V_{GS(th)}$         | gate-source threshold voltage | I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; <u>Fig. 9</u> ;<br><u>Fig. 10</u> |  | 1.4 | 1.7  | 2.1  | V    |
|                      |                               | I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; <u>Fig. 9</u>                    |  | -   | -    | 2.45 | V    |
|                      |                               | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}; Fig. 9$   |  | 0.5 | -    | -    | V    |
| I <sub>DSS</sub>     | drain leakage current         | V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C  |  | -   | 0.11 | 10   | μA   |
|                      |                               | V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C   |  | -   | -    | 500  | μA   |
| I <sub>GSS</sub>     | gate leakage current          | V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C   |  | -   | 2    | 100  | nA   |
|                      |                               | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C  |  | -   | 2    | 100  | nA   |
| R <sub>DSon</sub>    | drain-source on-state         | $V_{GS} = 5 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$  |  | -   | 12.1 | 15   | mΩ   |
|                      | resistance                    | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C;<br>Fig. 11                                   |  | -   | 11.6 | 14.7 | mΩ   |
|                      |                               | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 175 °C;<br>Fig. 12; Fig. 11                          |  | -   | -    | 41.4 | mΩ   |
| Dynamic cl           | naracteristics                |   |  |     |      |      |      |
| Q <sub>G(tot)</sub>  | total gate charge             | I <sub>D</sub> = 20 A; V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 5 V;<br>Fig. 13; Fig. 14                           |  | -   | 45.8 | -    | nC   |
| Q <sub>GS</sub>      | gate-source charge            |   |  | -   | 11   | -    | nC   |
| $Q_{GD}$             | gate-drain charge             |   |  | -   | 16   | -    | nC   |

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| Symbol              | Parameter                    | Conditions  |  | Min | Тур  | Max  | Unit |
|---------------------|------------------------------|---|--|-----|------|------|------|
| C <sub>iss</sub>    | input capacitance            | $V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$<br>$T_j = 25 \text{ °C}; Fig. 15$ |  | -   | 4604 | 6139 | pF   |
| C <sub>oss</sub>    | output capacitance           |   |  | -   | 269  | 323  | pF   |
| C <sub>rss</sub>    | reverse transfer capacitance | _   |  | -   | 156  | 213  | pF   |
| t <sub>d(on)</sub>  | turn-on delay time           | $V_{DS}$ = 80 V; $R_{L}$ = 4 $\Omega$ ; $V_{GS}$ = 5 V; $R_{G(ext)}$ = 5 $\Omega$                   |  | -   | 21   | -    | ns   |
| t <sub>r</sub>      | rise time                    |   |  | -   | 32   | -    | ns   |
| t <sub>d(off)</sub> | turn-off delay time          |   |  | -   | 85   | -    | ns   |
| t <sub>f</sub>      | fall time                    |   |  | -   | 59   | -    | ns   |
| Source-dra          | ain diode                    | 1   |  | 1   |      |      |      |
| $V_{SD}$            | source-drain voltage         | $I_S = 20 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$                      |  | -   | 8.0  | 1.2  | V    |
| t <sub>rr</sub>     | reverse recovery time        | $I_S$ = 20 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 25 V                          |  | -   | 44   | -    | ns   |
| Q <sub>r</sub>      | recovered charge             |   |  | -   | 79   | -    | nC   |

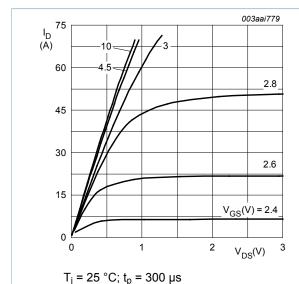


Fig. 6. Output characteristics; drain current as a

function of drain-source voltage; typical values

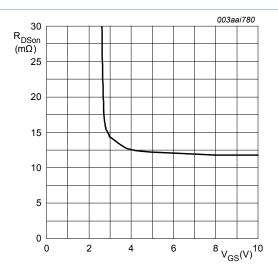


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 20A$$

#### N-channel 100 V, 15 mΩ logic level MOSFET in LFPAK56

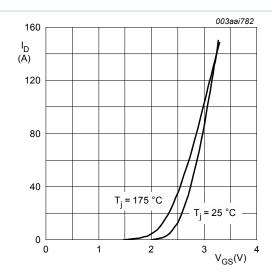


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



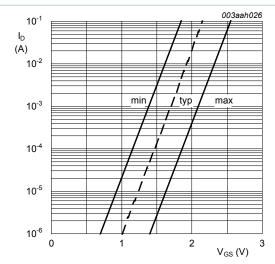


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

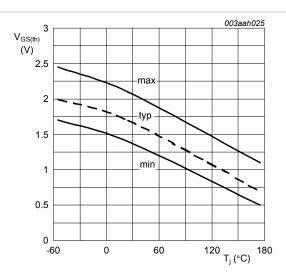
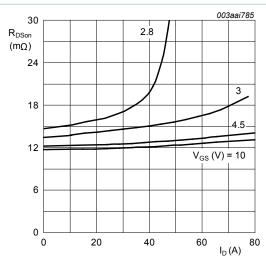


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D$$
 = 1 mA;  $V_{DS}$  =  $V_{GS}$ 



 $T_i = 25 \, ^{\circ}C; t_p = 300 \, \mu s$ 

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

#### N-channel 100 V, 15 mΩ logic level MOSFET in LFPAK56

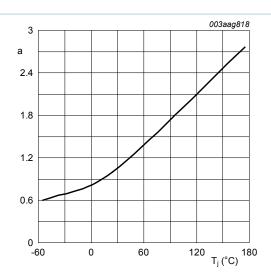


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25 °C)}}$$

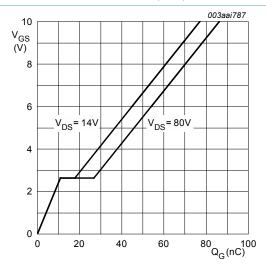


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_i = 25$$
°C;  $I_D = 20A$ 

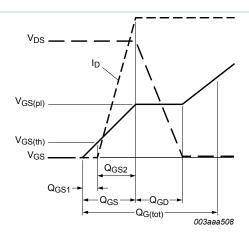


Fig. 13. Gate charge waveform definitions

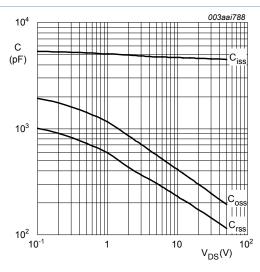


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V$$
;  $f = 1MHz$ 

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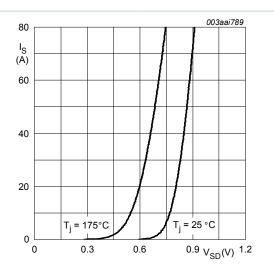
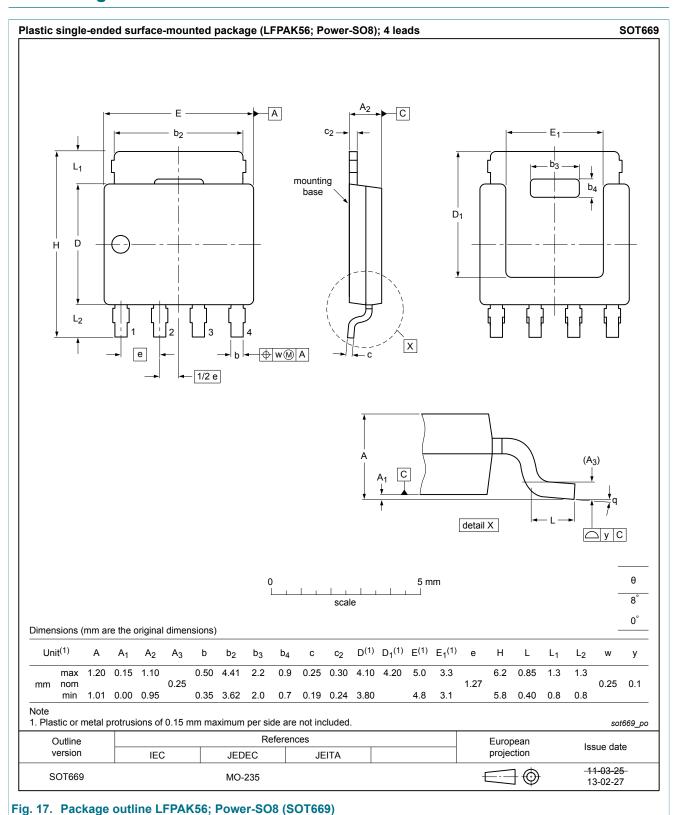


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

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# 11. Package outline



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### 12. Legal information

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